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### **MMBT3906T** PNP Epitaxial Silicon Transistor

### Features

- General purpose amplifier transistor.
- Ultra-Small Surface Mount Package for all types.
- Suitable for general switching & amplification
- Well suited for portable application
- As complementary type, NPN MMBT3904T is recommended

### Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-40	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	200	mA
ТJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 ~ 150	°C
	Istorage Temperature Range are limiting values above which the serviceability of any semiconduct		

These ratings are limiting values above which the serviceability of any semiconductor device may be impared.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics\* Ta=25°C unless otherwise noted

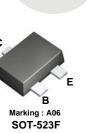
Symbol	Parameter	Max	Unit
P <sub>C</sub>	Collector Power Dissipation, by $R_{\theta JA}$	250	mW
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	500	°C/W

\* Minimum land pad.

### Electrical Characteristics\* T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Unit
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = -10\mu A, I_{\rm E} = 0$	-40		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = -1 {\rm mA},  I_{\rm B} = 0$	40		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = -10\mu A, I_{C} = 0$	-5		V
I <sub>CEX</sub>	Collector Cut-off Current	$V_{CE} = -30V, V_{EB(OFF)} = -0.3V$		-50	nA
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 1V, I_{C} = -0.1mA$ $V_{CE} = 1V, I_{C} = -1mA$ $V_{CE} = 1V, I_{C} = -10mA$ $V_{CE} = 1V, I_{C} = -50mA$ $V_{CE} = 1V, I_{C} = -100mA$	60 80 100 60 30	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_{C} = -10mA$ , $I_{B} = -1mA$ $I_{C} = -50mA$ , $I_{B} = -5mA$		-0.25 -0.4	V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5mA	-0.65	-0.85 -0.95	V V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -20V, I <sub>C</sub> = -10mA, f = 100MHz	250		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -5V, I_E = 0, f = 1MHz$		7.0	pF
C <sub>ib</sub>	Input Capacitance	$V_{EB} = -0.5V, I_{C} = 0, f = 1MHz$		15	pF
t <sub>d</sub>	Delay Time	$V_{CC} = -3V, I_C = -10mA$		35	ns
t <sub>r</sub>	Rise Time	I <sub>B1</sub> =- I <sub>B2</sub> = -1mA		35	ns
t <sub>s</sub>	Storage Time			225	ns
t <sub>f</sub>	Fall Time			75	ns

\* DC Item are tested by Pulse Test : Pulse Width≤300us, Duty Cycle≤2%



February 2008

## MMBT3906T — PNP Epitaxial Silicon Transistor

Ic=10\*lb

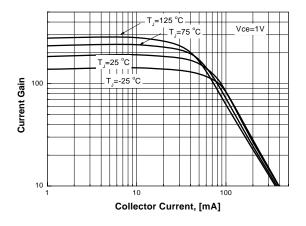
T\_=25 °C

-25 °C

100

### **Typical Performance Characteristics**

### Figure 1. DC Current Gain





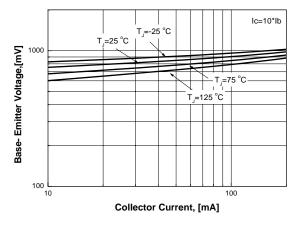


Figure 5. Collector- Base Capacitance

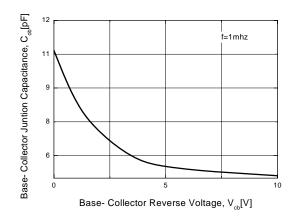


Figure 4. Collector- Base Leakage Current

Figure 2. Collector-Emitter Saturation Voltage

T<sub>J</sub>=125 °C

.=75

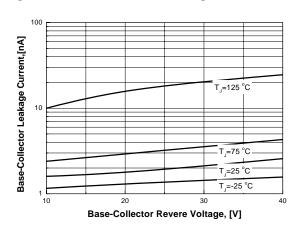
Collector Current, [mA]

1000

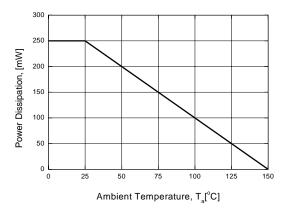
Collector-Emitter Voltage,[mV]

100

10





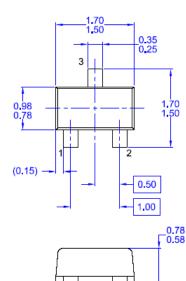


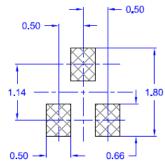
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### **Package Dimensions**

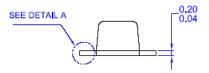
### SOT-523F

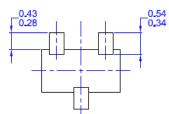
- Case : SOT-523F
- Case Material(Molded Plastic): KTMC1060SC
- UL Flammability classification rating : "V0"
- Moisture Sensitivity level per JESD22-A1113B : MSL 1
- Lead terminals solderable per MIL-STD7502026 /JESD22A121
- Lead Free Plating : Pure Tin(Matte)





LAND PATTERN RECOMMENDATION





**Dimensions in Millimeters** 

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SEMICONDUCTOR

# MMBT3906T PNP Epitaxial Silicon Transistor

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